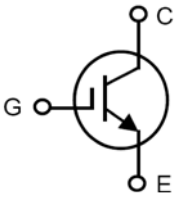
IXYS

1200V XPT™ IGBTs GenX3™

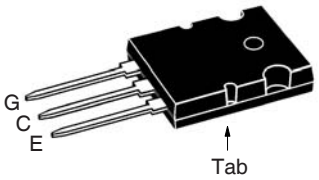
IXYK120N120C3
IXYX120N120C3

V_{CES} = 1200V
I_{C110} = 120A
$V_{CE(sat)}$ ≤ 3.20V
$t_{fi(typ)}$ = 96ns

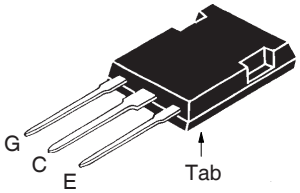
High-Speed IGBTs
for 20-50 kHz Switching



TO-264 (IXYK)



PLUS247 (IXYX)



G = Gate E = Emitter
C = Collector Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 175°C	1200	V
V_{CGR}	T_J = 25°C to 175°C, R_{GE} = 1MΩ	1200	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C= 25°C (Chip Capability)	240	A
I_{LRMS}	Terminal Current Limit	160	A
I_{C110}	T_C= 110°C	120	A
I_{CM}	T_C = 25°C, 1ms	700	A
I_A	T_C = 25°C	60	A
E_{AS}	T_C = 25°C	2	J
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 150°C, R_G = 1Ω Clamped Inductive Load	I_{CM} = 240 $V_{CE} \leq V_{CES}$	A
P_C	T_C = 25°C	1500	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in
F_C	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb
Weight	TO-264	10	g
	PLUS247	6	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	1200			V
$V_{GE(th)}$	I_C = 500μA, V_{CE} = V_{GE}	3.0		5.0	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			25	μA
	T_J = 150°C			1.5	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = I_{C110}, V_{GE} = 15V, Note 1		2.55	3.20	V
	T_J = 150°C		3.40		V

Features

- Optimized for Low Switching Losses
- Square RBSOA
- International Standard Packages
- Positive Thermal Coefficient of Vce(sat)
- Avalanche Rated
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

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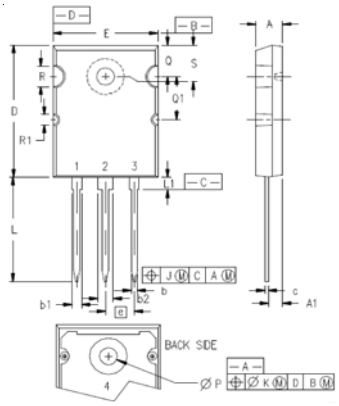
Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
g_{fs}	I_C = 60A, V_{CE} = 10V, Note 1	40	68	S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		9850	pF
C_{oes}			580	pF
C_{res}			218	pF
$Q_{g(on)}$	$I_C = I_{C110}$, V_{GE} = 15V, $V_{CE} = 0.5 \bullet V_{CES}$		412	nC
Q_{ge}			73	nC
Q_{gc}			180	nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		35	ns
t_{ri}	I_C = 100A, V_{GE} = 15V		77	ns
E_{on}	$V_{CE} = 0.5 \bullet V_{CES}$, $R_G = 1\Omega$		6.75	mJ
$t_{d(off)}$	Note 2		176	ns
t_{fi}			96	ns
E_{off}			5.10	mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		33	ns
t_{ri}	I_C = 100A, V_{GE} = 15V		72	ns
E_{on}	$V_{CE} = 0.5 \bullet V_{CES}$, $R_G = 1\Omega$		10.30	mJ
$t_{d(off)}$	Note 2		226	ns
t_{fi}			120	ns
E_{off}			7.20	mJ
R_{thJC}				0.10 °C/W
R_{thCS}			0.15	°C/W

Notes:

1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

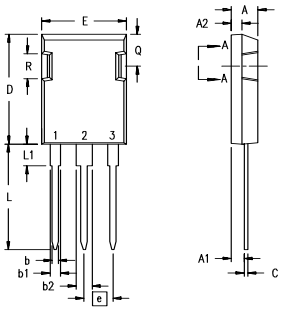
TO-264 Outline



Terminals: 1 = Gate
2,4 = Collector
3 = Emitter

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS247™ Outline



Terminals: 1 - Gate
2 - Collector
3 - Emitter

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ T_J = 25ºC

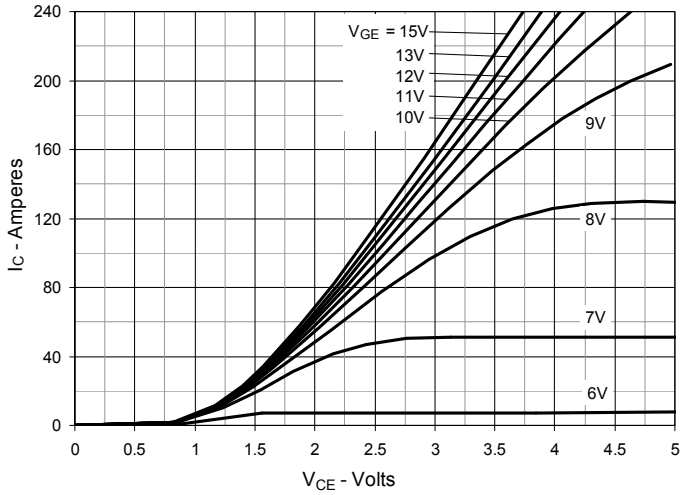


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

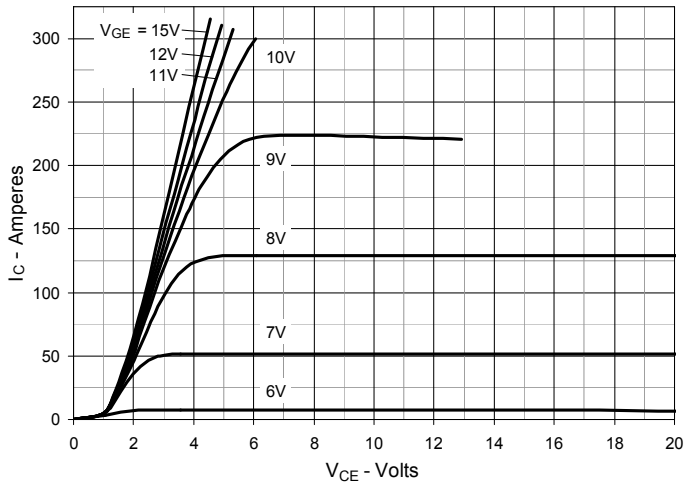


Fig. 3. Output Characteristics @ T_J = 150ºC

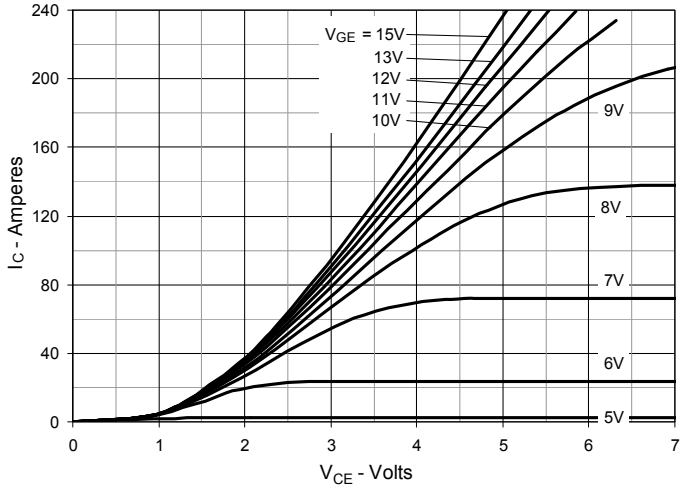


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

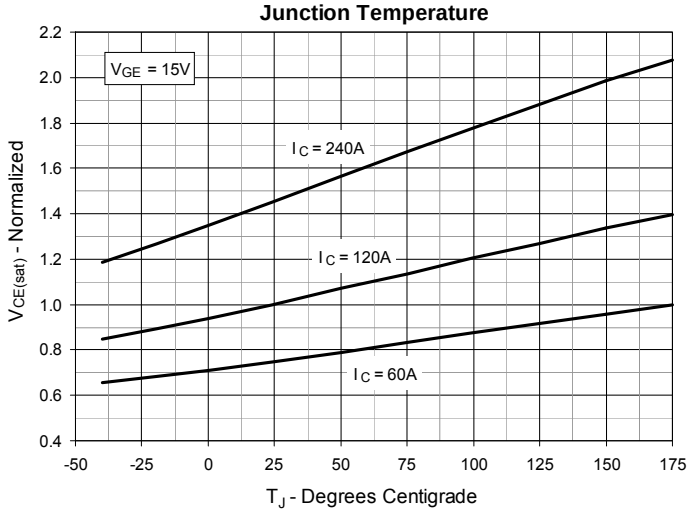


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

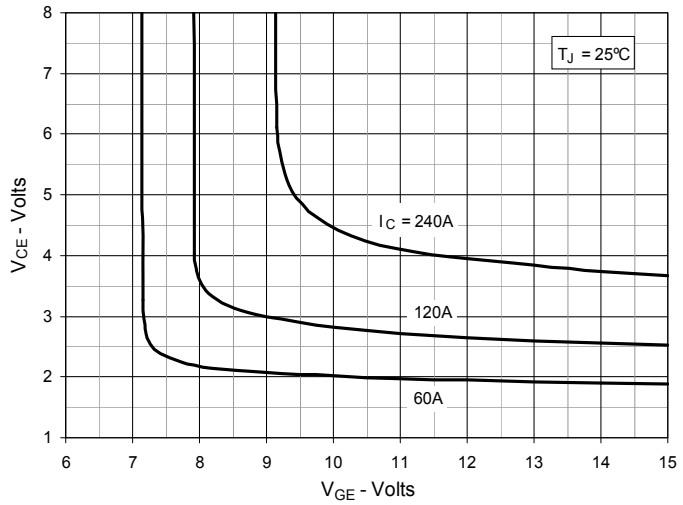


Fig. 6. Input Admittance

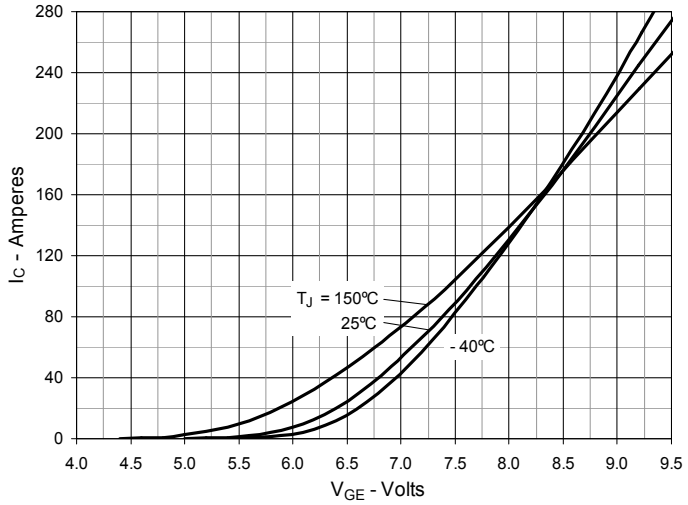


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Fig. 7. Transconductance

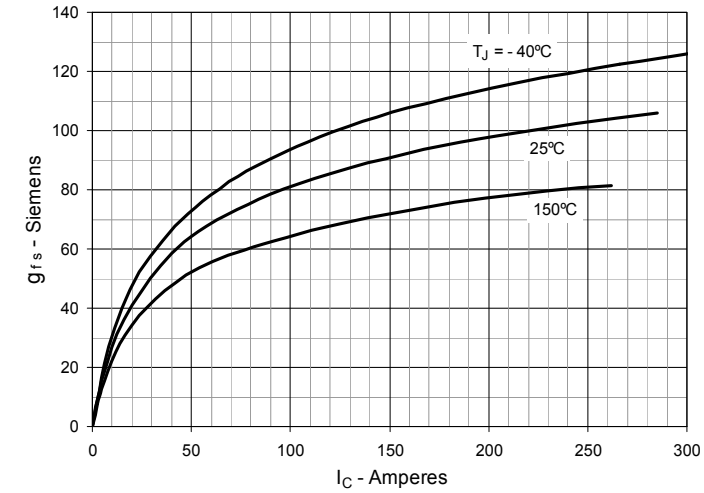


Fig. 8. Gate Charge

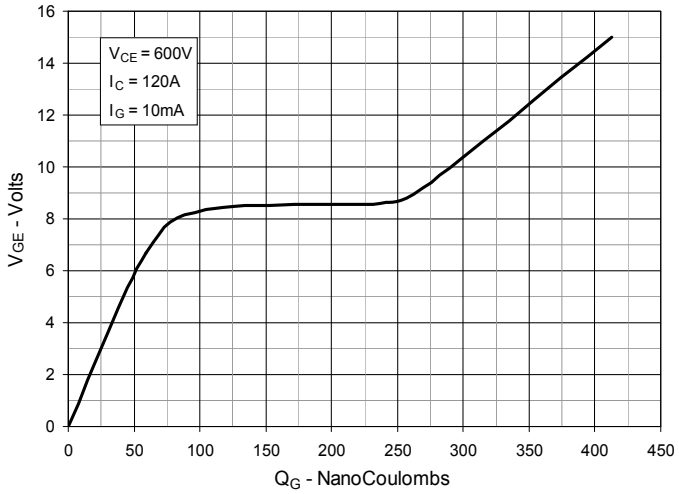


Fig. 9. Capacitance

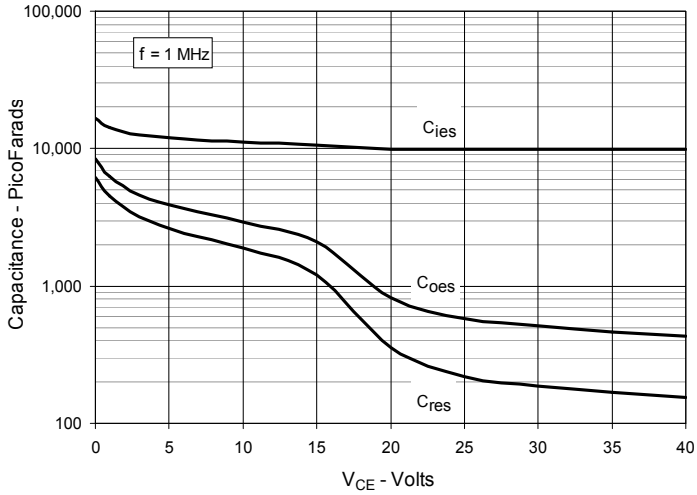


Fig. 10. Reverse-Bias Safe Operating Area

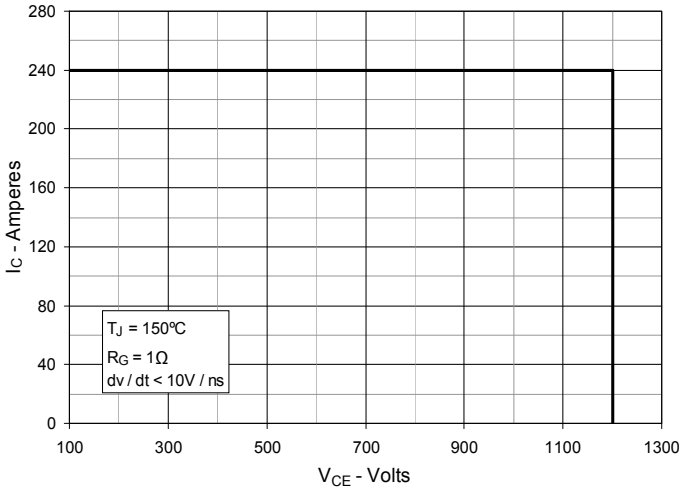
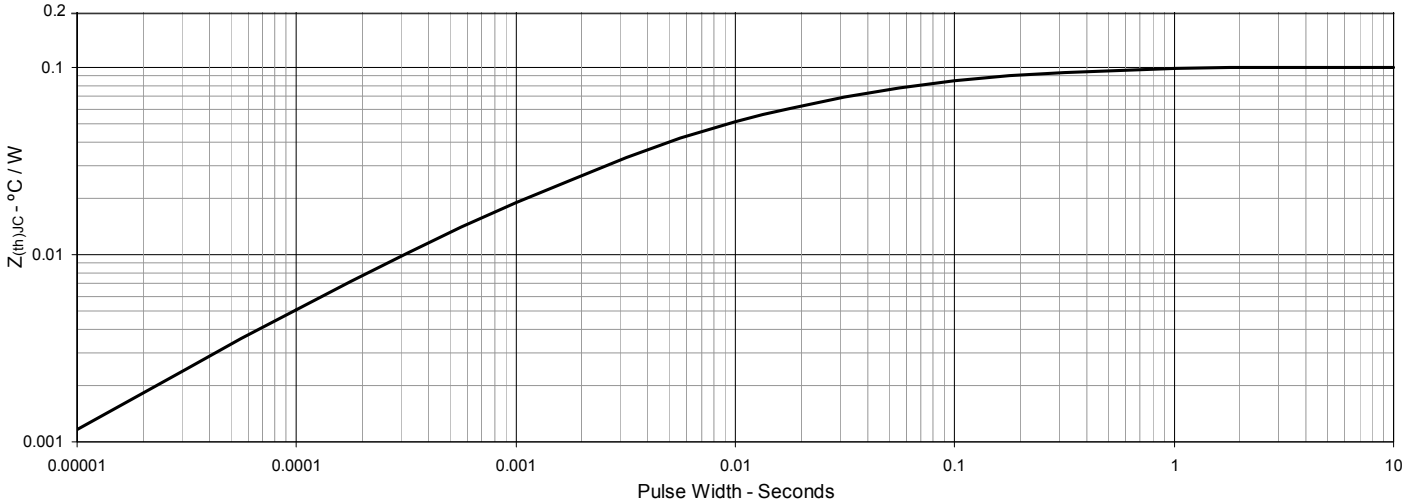


Fig. 11. Maximum Transient Thermal Impedance



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

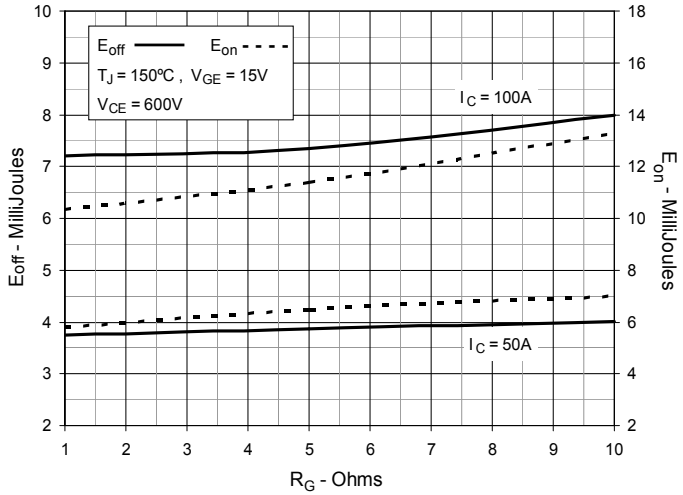


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

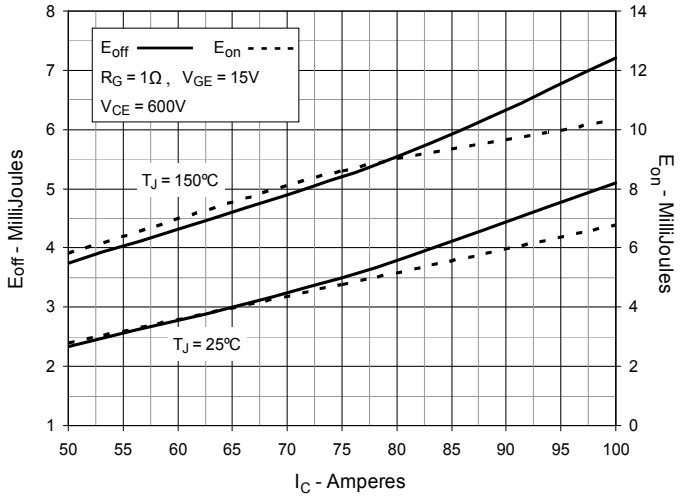


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

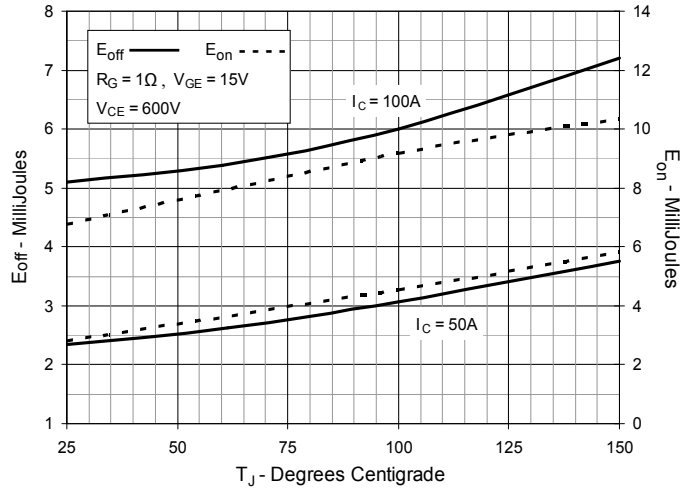


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

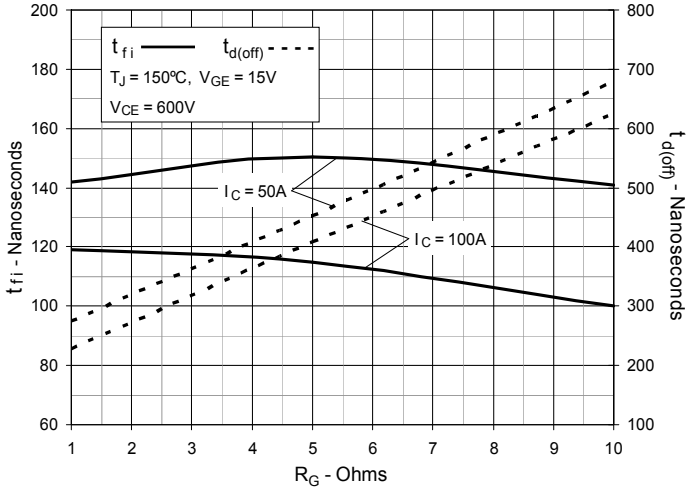


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

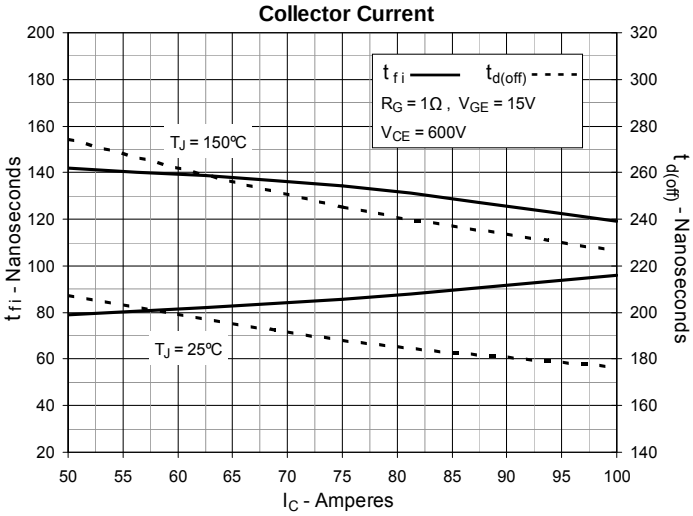


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

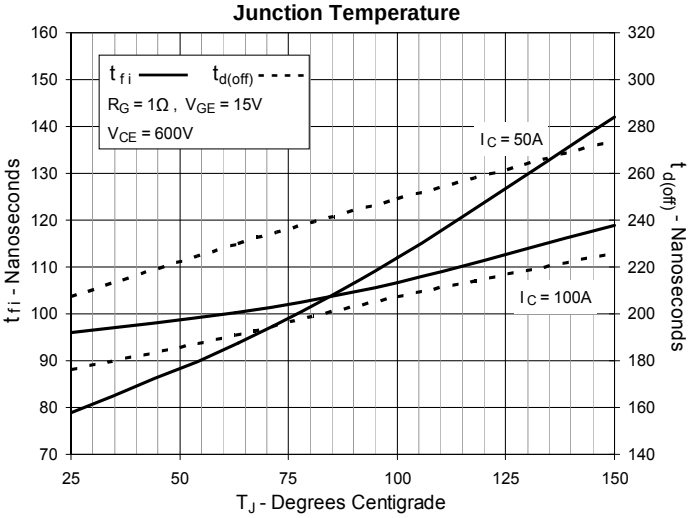


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Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

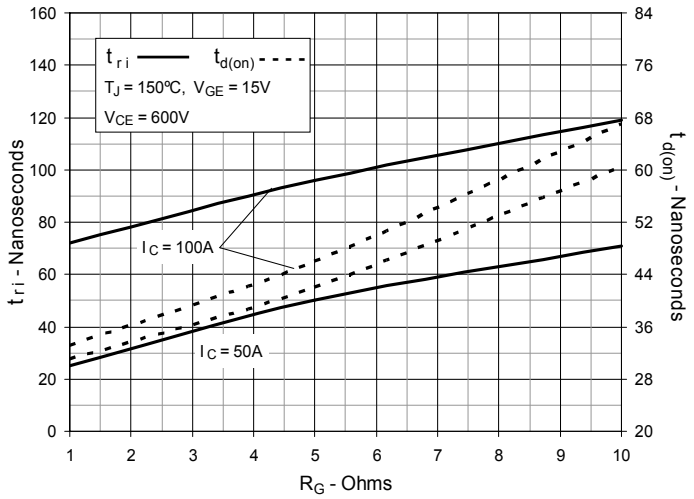


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

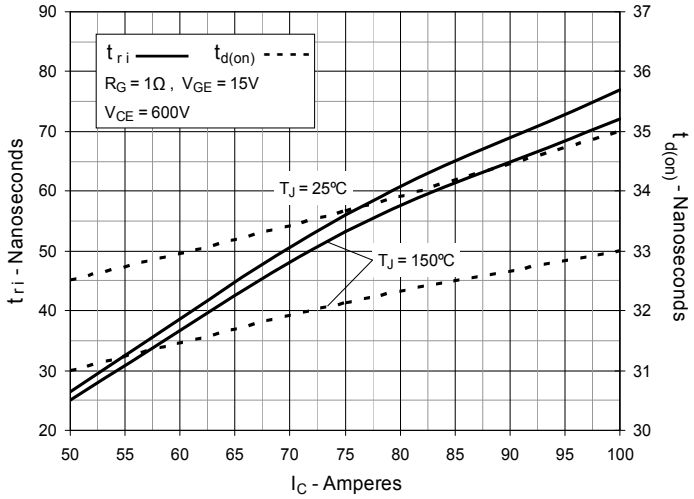


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

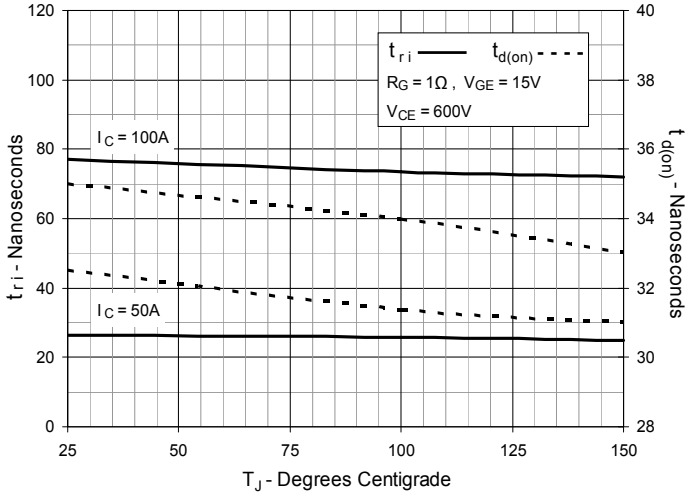
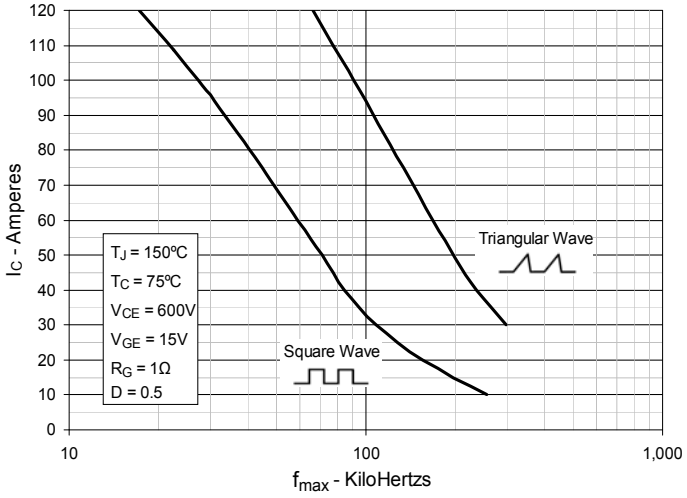


Fig. 21. Maximum Peak Load Current vs. Frequency



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